



	« UNIBOND™ » WAFERS	
Quality : PRIME	Diameter : 200mm	
Commercial Part  xxxx-xxx-01		
Product description : 5000/10000Å +/-200Å - base HR		

Top silicon layer

Parameters	Measurement equipment /conditions	Min	Target	Max	Unit
Metrology edge exclusion	All parameters			5	mm
SOI mean thickness +/- 3sigma	(2)	480	500	520	nm
Conductivity type	P type				
Dopant	Boron				
Resistivity	SEMI M1 (1)	8.5		11.5	Ohmcm
Crystal orientation	SEMI M1 (1)	-0.5	(100)	+0.5	deg
Crystal Growth Method	CZ cop free				
Light Point Defects (LPD)	SP1>0.2µm threshold (2)			200	Count
Area Count (LAD)	SP1>0.8µm threshold (2)			30	Count
Bonding voids	Visual inspection > 0.5 mm diameter (2)			none	Count
Surface defects (visual)	Edge chips, scratch, slip, stain (2)			none	Count
HF Defects	(2)			1	DEF/cm ²
surface contamination_Fe	VPD-ICPMS (2)			5	E10 at/cm ²
surface contamination_Cu	VPD-ICPMS (2)			5	E10 at/cm ²
surface contamination_Cr	VPD-ICPMS (2)			5	E10 at/cm ²
surface contamination_Ni	VPD-ICPMS (2)			5	E10 at/cm ²
surface metal contamination_Zn	VPD-ICPMS (2)			5	E10 at/cm ²
surface	VPD-ICPMS (2)			5	E10

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contamination_Na					at/cm ²
surface contamination_Ca	VPD-ICPMS (2)			5	E10 at/cm ²
surface contamination_Al	VPD-ICPMS (2)			5	E10 at/cm ²
Surface roughness	Mirror polished				

Buried oxide



Parameters	Measurement equipment /conditions	Min	Target	Max	Unit
Metrology edge exclusion	All parameters			5	mm
Mean thickness	(2)	900	1000	1100	nm
Within wafer thickness standard deviation	(2)			4	nm

Mechanical parameters

Parameters	Measurement equipment /conditions	Min	Target	Max	Unit
Metrology edge exclusion	All parameters			5	mm
Thickness	SEMI M1 (1)	710	725	740	µm
Diameter	SEMI M1 (1)	199.8	200	200.2	mm
TTV	(1)			5	µm
SFQR max	Site size : 25 x 25 mm (1)			0.15	µm
Warp	(2)			60	µm

Handle wafer

Parameters	Measurement equipment /conditions	Min	Target	Max	Unit
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Metrology edge exclusion	All parameters			5	mm
Notch orientation axis	SEMI M1 (1)	-1	<110>	+1	deg
Conductivity type	N/A				
Resistivity	SEMI M1 (1)	750	1000		Ohmcm
Crystal orientation	SEMI M1 (1)	-0.5	(100)	+0.5	deg
Crystal Growth Method	Standard CZ				
Carbon Content	ASTM F1391 (1)			0.3	ppma
Oxygen Content	ASTM F1188 (1) - max : N/S	13			new ppma
Backside surface	WSB / Oxidized				
Lasermark	backside				



(1) Data based on bulk silicon measurements(2) Data based on Soitec internal measurements procedure

Packing & Labelling

Packaging boxes are Ultrapak boxes. Maximum wafer number per box is 25. Double vacuum seal protects each box. Transport packaging are reinforced by cardboard containers, in which the boxes are held in place and protected by performed shells. Two labels are affixed, one on the inner Ultrapak box and the other one on the outer aluminum bag. Labels contain commercial part reference, quantity, production date, lot number and additional product information.

General Information

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